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Attn: Theresa Doan

Patent Examining Corps

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FAX NUMBER 703-872-9306FROM: Eric H. OlsonOUR REF: 303.355US4

TELEPHONE: 612-371-2131

\* Please deliver to Examiner Theresa Doan in Art Unit 2814. \*

Total pages of this transmission, including cover letter: 12 pgs.

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In re. Patent Application of: Leonard Forbes et al.Examiner: Theresa DoanSerial No.: 09/883,795Group Art Unit: 2814Filed: June 18, 2001Docket No.: 303.355US4Title: METHOD OF FORMING A DEVICE WITH A GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE

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PATENT

S/N UnknownIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al. Examiner: Unknown  
Serial No.: Unknown Group Art Unit: Unknown  
Filed: Herewith Docket: 303.355US4  
Title: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM  
ALUMINUM NITRIDE GATE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
Washington, D.C. 20231

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for review in connection with the above-identified patent application. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner be returned to the Applicants.

In accordance with 37 C.F.R. § 1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 09/141,392, filed on August 27, 1998, which is relied upon for an earlier filing date under 35 U.S.C. § 120.

Applicants respectfully request consideration of these references during prosecution of the above-identified matter. The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

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Date

18 JUNE 2001

By

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Sheet 1 of 11

Form 1449\*

Atty. Docket No.: 303.355US4

Serial No. Unknown

INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT  
(Use several sheets if necessary)

Applicant: Leonard Forbes et al.

Filing Date: Herewith

Group: Unknown

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Examiner

Date Considered

\*Substitute Disclosure Statement Form (PTO-1449)

\*\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 2 of 11

Form 1449*	Atty. Docket No.: 303,355US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

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Sheet 3 of 11

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	Filing Date: Herewith	Group: Unknown

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\*Substitute Disclosure Statement Form (FID-1449)

\*\*EXAMINER: INITIAL if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 4 of 11

Form 1449*	Any. Docket No.: 303.355US4	Serial No. Unknown
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\*\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 603; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 5 of 11

Form 1449*	Atty. Docket No.: 303.355US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

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Sheet 6 of 11

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Initial

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\*Substitute Disclosure Statement Form (PTO-1449)

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Sheet 7 of 11

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	Filing Date: Herewith	Group: Unknown

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(Including Author, Title, Date, Pertinent Pages, Etc.)

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Sheet 8 of 11

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Sheet 9 of 11

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Sheet 10 of 11

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
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